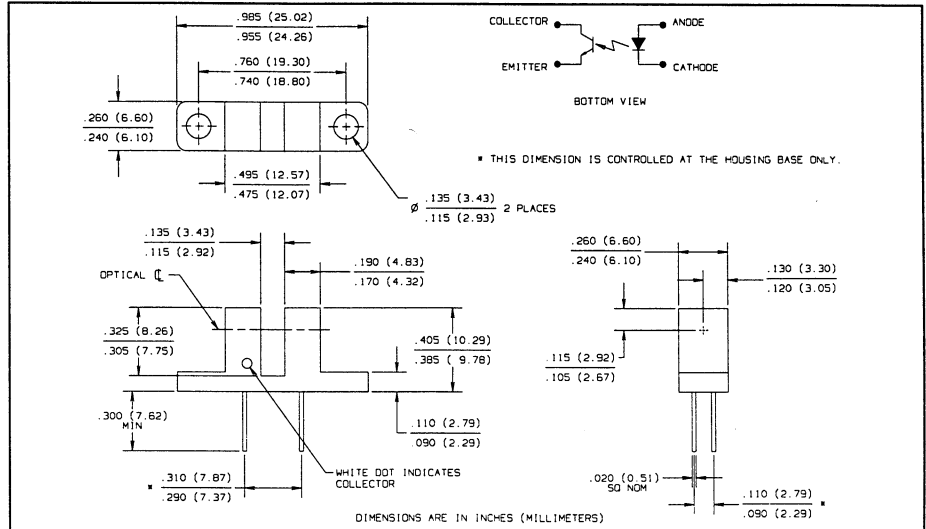
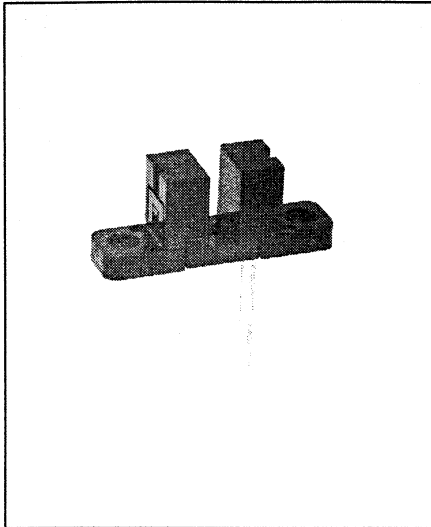


Slotted Optical Switches

Types OPB844A, OPB844B



Features

- Non-contact switching
- Printed circuit board mounting
- 0.125" (3.18 mm) wide slot
- 0.300" (7.62 mm) lead spacing
- Transmissive plastic housing

Description

The OPB844 series consists of an infrared emitting diode and an NPN silicon phototransistor mounted on opposite sides of a .125" (3.18 mm) wide slot. The inexpensive plastic housing is transmissive to infrared and provides for environmental protection from dust and contamination. The "A" option is unapertured, while the "B" version offers a .010" (0.254 mm) wide aperture located over the phototransistor for improved resolution. Phototransistor switching takes place whenever an opaque object passes through the slot.

OPB#	Phototransistor Aperture Width
OPB844A	.040"
OPB844B	.010"

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Storage and Operating Temperature Range -40°C to $+85^\circ\text{C}$
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron]. $240^\circ\text{C}^{(1)}$

Input Diode

Forward DC Current 50 mA
Peak Forward Current (1 μs pulse width, 300 pps) 3.0 A
Reverse DC Voltage 2.0 V
Power Dissipation 100 mW⁽²⁾

Output Phototransistor

Collector-Emitter Voltage 30 V
Emitter-Collector Voltage 5.0 V
Collector DC Current 30 mA
Power Dissipation 100 mW⁽²⁾

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering.
- (2) Derate Linearly 1.67 mW/ $^\circ\text{C}$ above 25°C .
- (3) All parameters tested using pulse technique.
- (4) Methanol or isopropanol are recommended as cleaning agents. Plastic housing is soluble in chlorinated hydrocarbons and ketones.

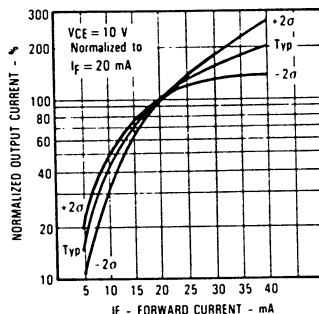
Types OPB844A, OPB844B

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

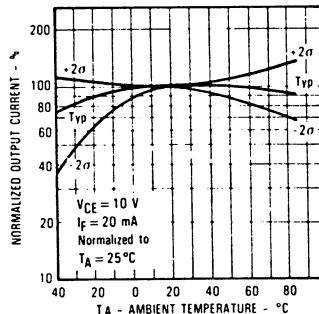
SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
Input Diode					
V_F	Forward Voltage		1.7	V	$I_F = 20\text{ mA}$
I_R	Reverse Current		100	μA	$V_R = 2\text{ V}$
Output Phototransistor					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	30		V	$I_C = 1\text{ mA}$
$V_{(BR)ECO}$	Emitter-Collectro Breakdown Voltage	5.0		V	$I_E = 100\text{ }\mu\text{A}$
I_{CEO}	Collector-Emitter Dark Current		100	nA	$V_{CE} = 10\text{ V}, I_F = 0, E_e = 0$
Coupled					
$V_{CE(SAT)}$	Saturation Voltage		0.6	V	$I_C = 1800\text{ }\mu\text{A}, I_F = 20\text{ mA}$
$I_{C(ON)}$	On-State Collector Current	1800		μA	$V_{CE} = 0.6\text{ V}, I_F = 20\text{ mA}$

Typical Performance Curves

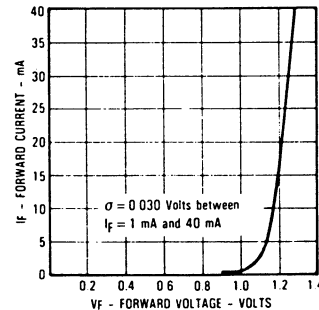
Normalized Output Current vs Forward Current



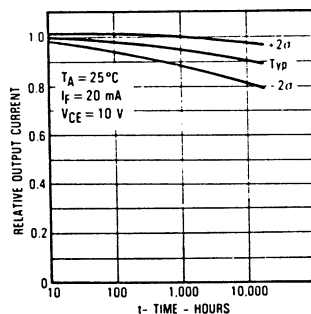
Normalized Output Current vs Ambient Temperature



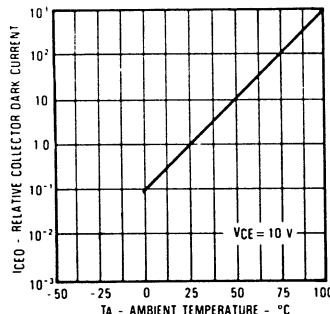
Forward Current vs Forward Voltage Input Diode



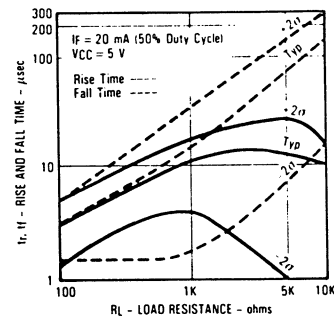
Relative Output Current vs Time



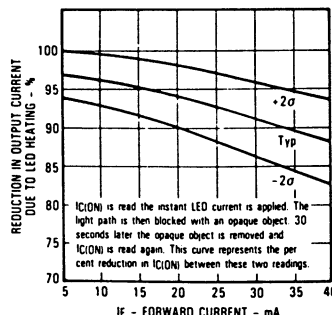
Collector Dark Current vs Ambient Temperature



Rise and Fall Time vs Load Resistance



Reduction in Output Current Due to LED Heating vs Forward Current



SLOTTED
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Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

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